

AIDA

Advanced European Infrastructures
for Detectors at Accelerators

WP9.4 micro-strip advanced ideas



I.Vila (IFCA-CSIC)

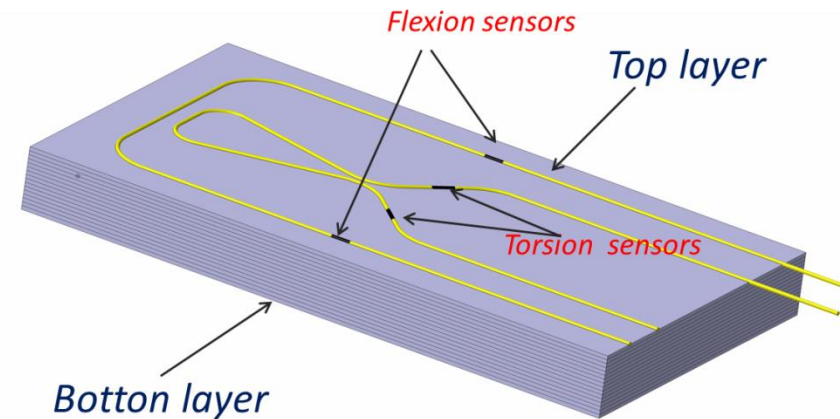
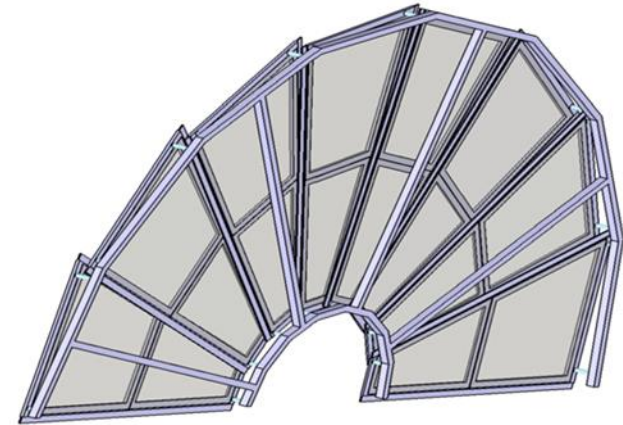
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I. Vila (ivan.vila@csic.es), IFCA/CSIC, AIDA Final Annual Meeting

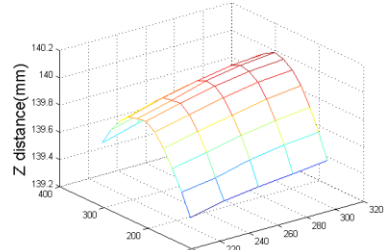
- Intro to the “advanced” strip studies.
- **Mechanics:** Self-monitoring CFRP structures.
- **Sensors:** 2D PSD strip sensors.
- **FE electronics:** long-shaping time ASIC

- Generic RD studies towards a ultralight strip tracking but aiming to fit the requirements for a Linear Collider Tracker
- Not aimed to for a deliverable.
- Covering several aspects: sensors, mechanics, FE ASIC, powering.

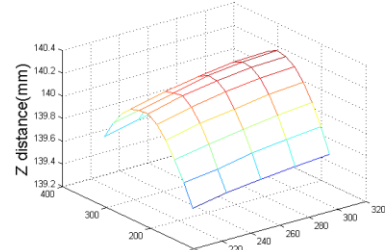
- The aim is to manufacture the ILD forward tracker support petals with integrated FOS
- Synergy with WP9.3 deliverable
- Intermediate step: shape measurement of CFRP plate with FOS embedded



CMM measurements of flexion calibration $z = 0.8$ mm CMM measurements of flexion calibration $z = 1$ mm

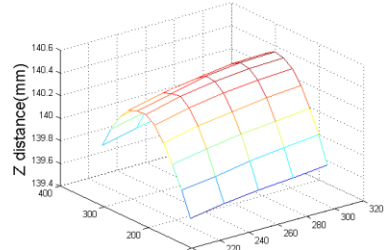


Y distance(mm) X distance (mm)

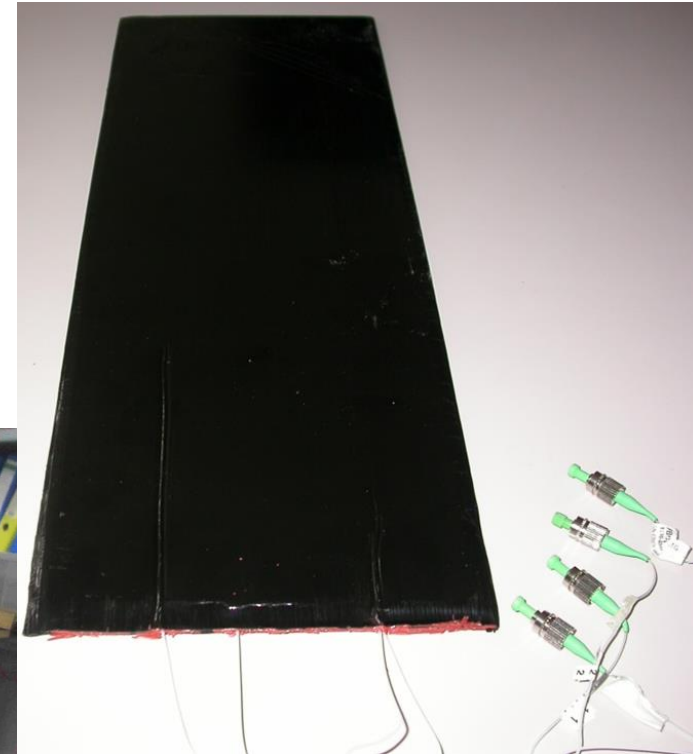
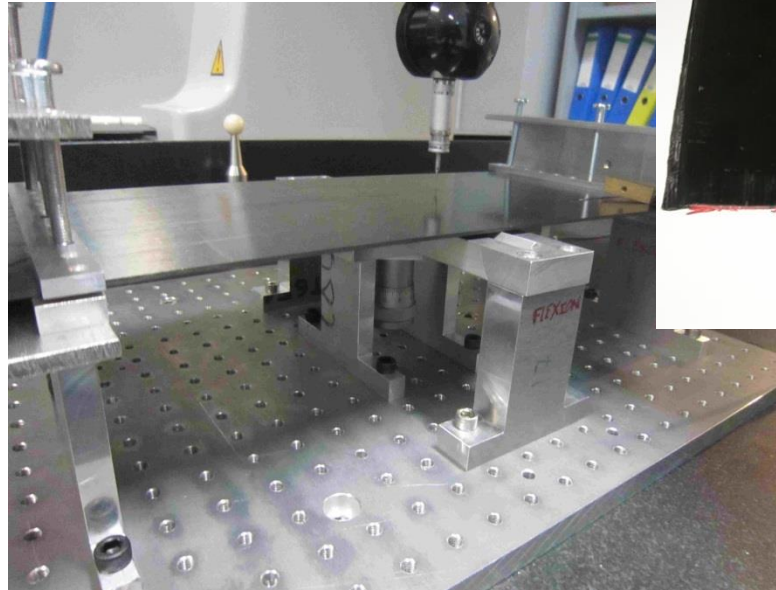


Y distance(mm) X distance (mm)

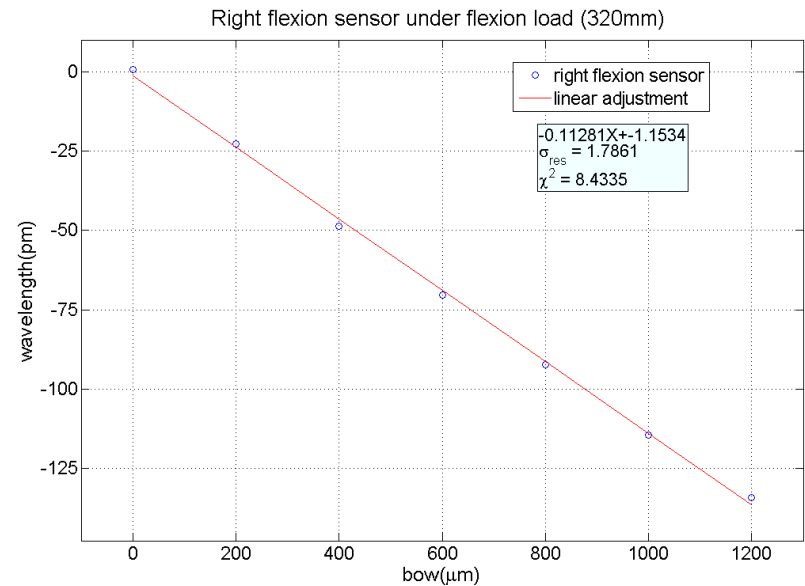
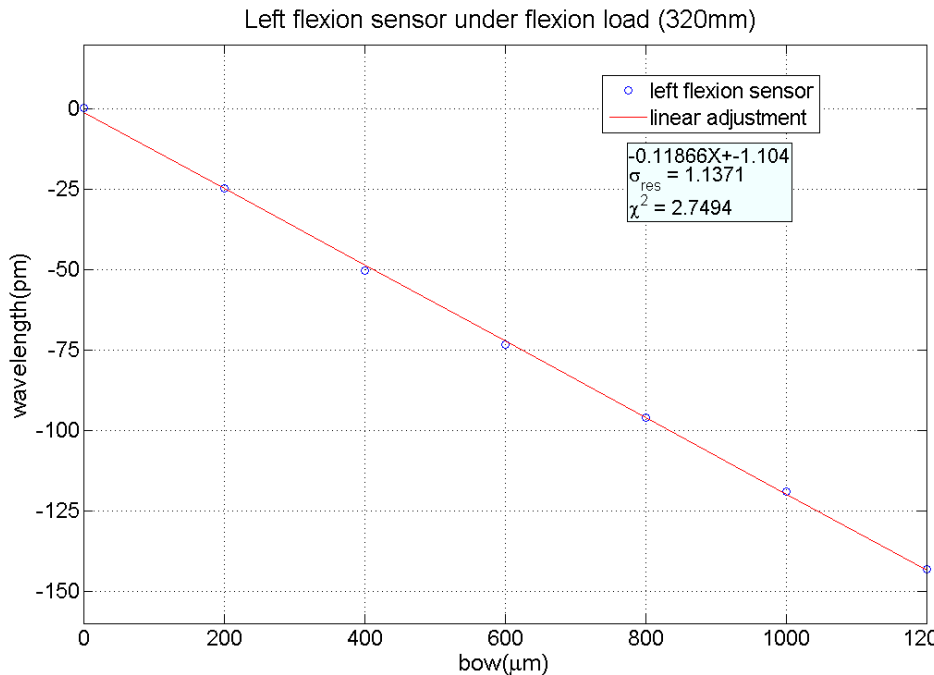
CMM measurements of flexion calibration $z = 1.2$ mm



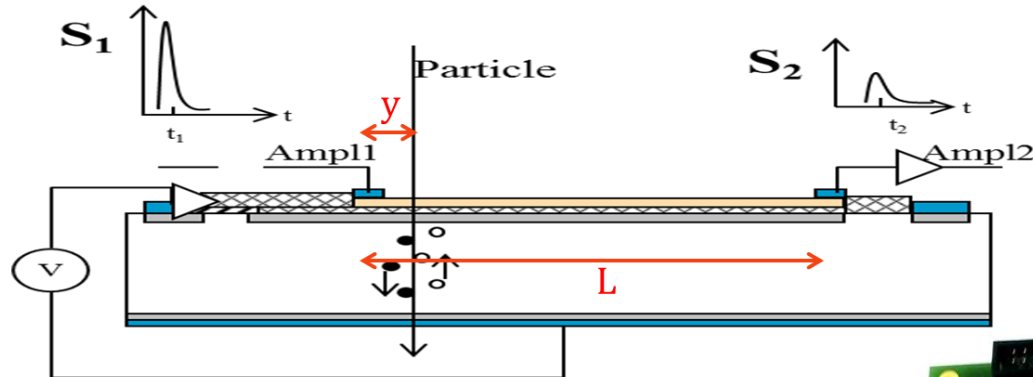
Y distance(mm) X distance (mm)



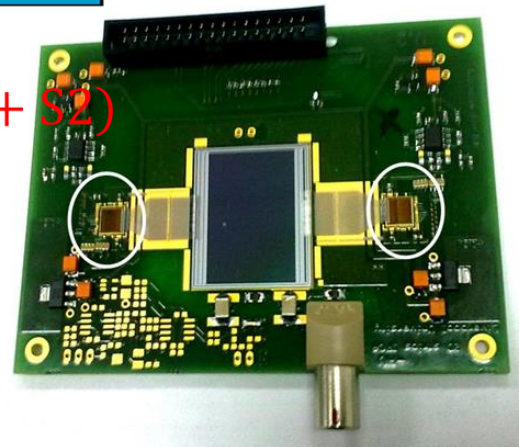
- Determining plate bow with resolution $\sim 10\mu\text{m}$



- Charge division used in wire chambers to determine the coordinate along the sensing wire.
- Same concept with conventional microstrips with slightly resistive electrodes (doped polysilicon)



$$\text{Fractional Position} \equiv y/L = S2/(S1 + S2)$$



Strip:

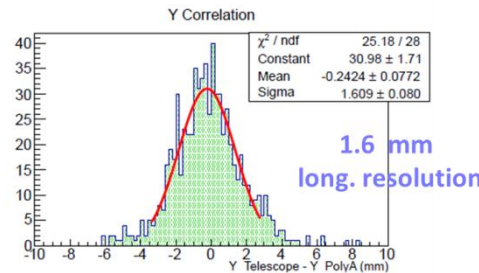
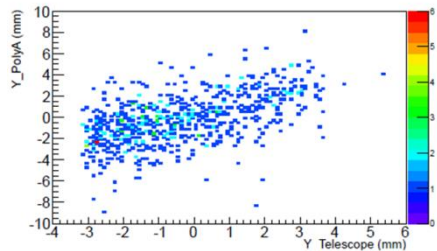
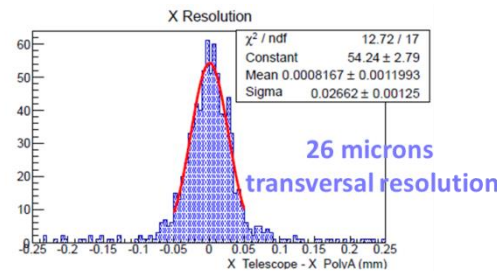
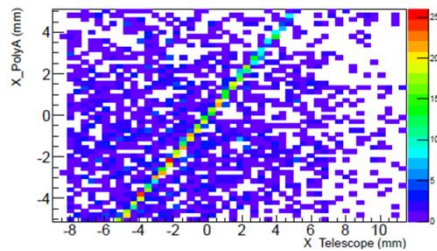
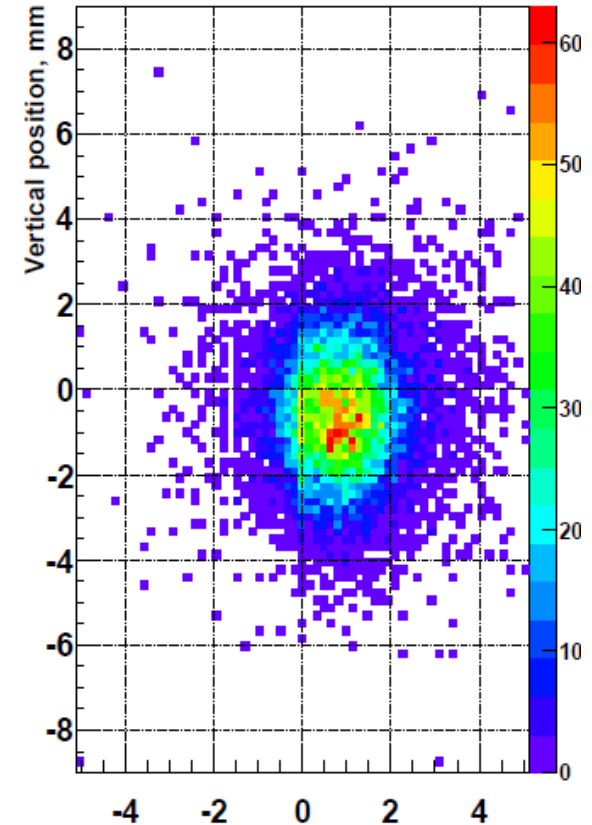
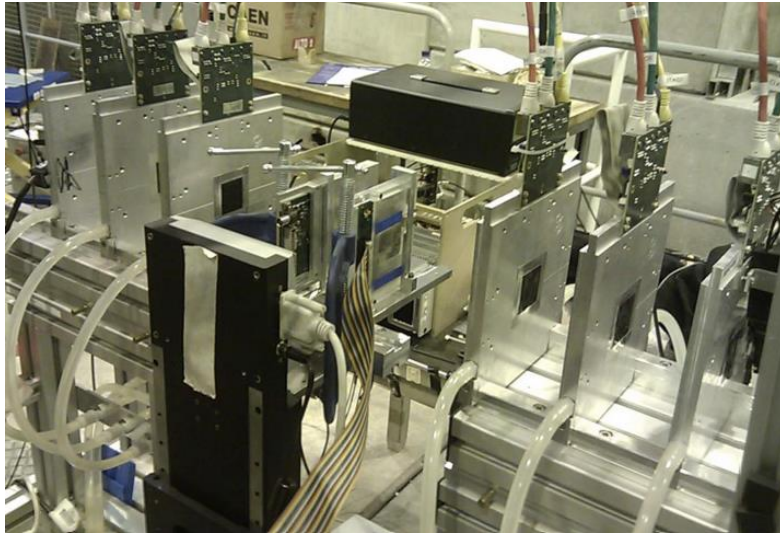
length = 20 mm
width = 20 μm

Pitches:

Implant = 80 μm
readout = 80 μm

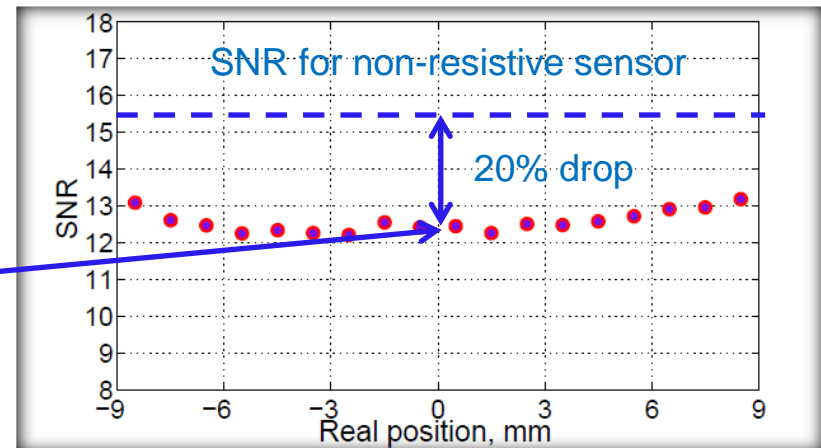
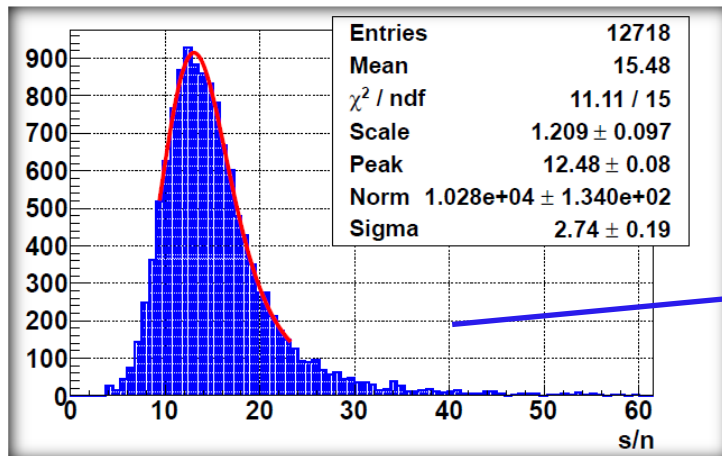
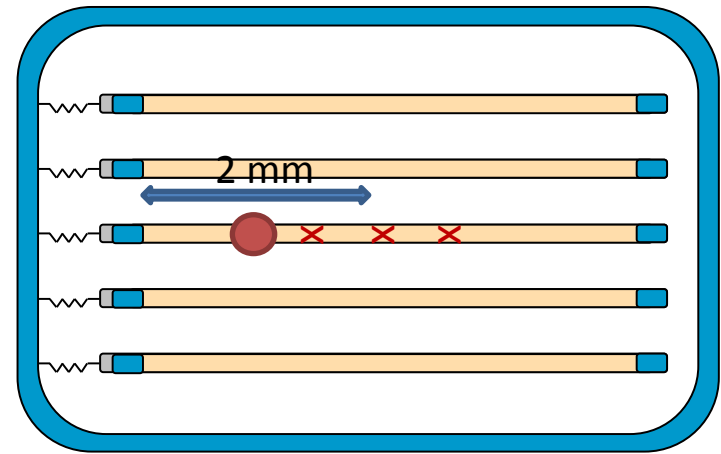
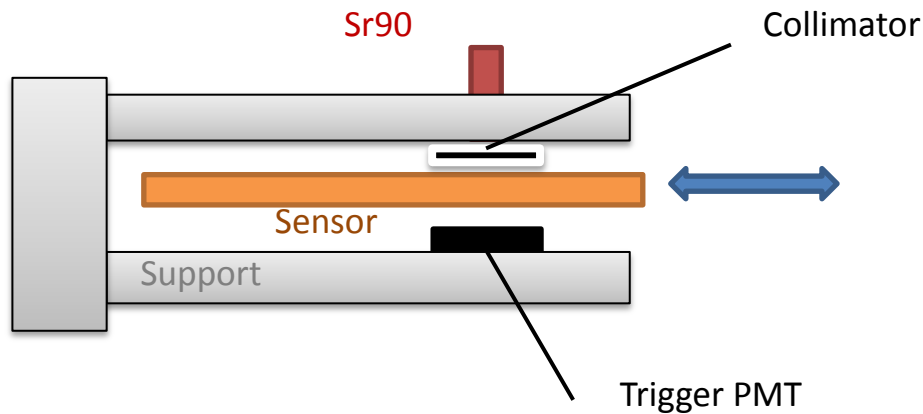
Electrode:

$R/\mu\text{m} = 2.8 \text{ Ohms}/\mu\text{m}$
 $R/\mu\text{m} = 12.2 \text{ Ohms}/\mu\text{m}$

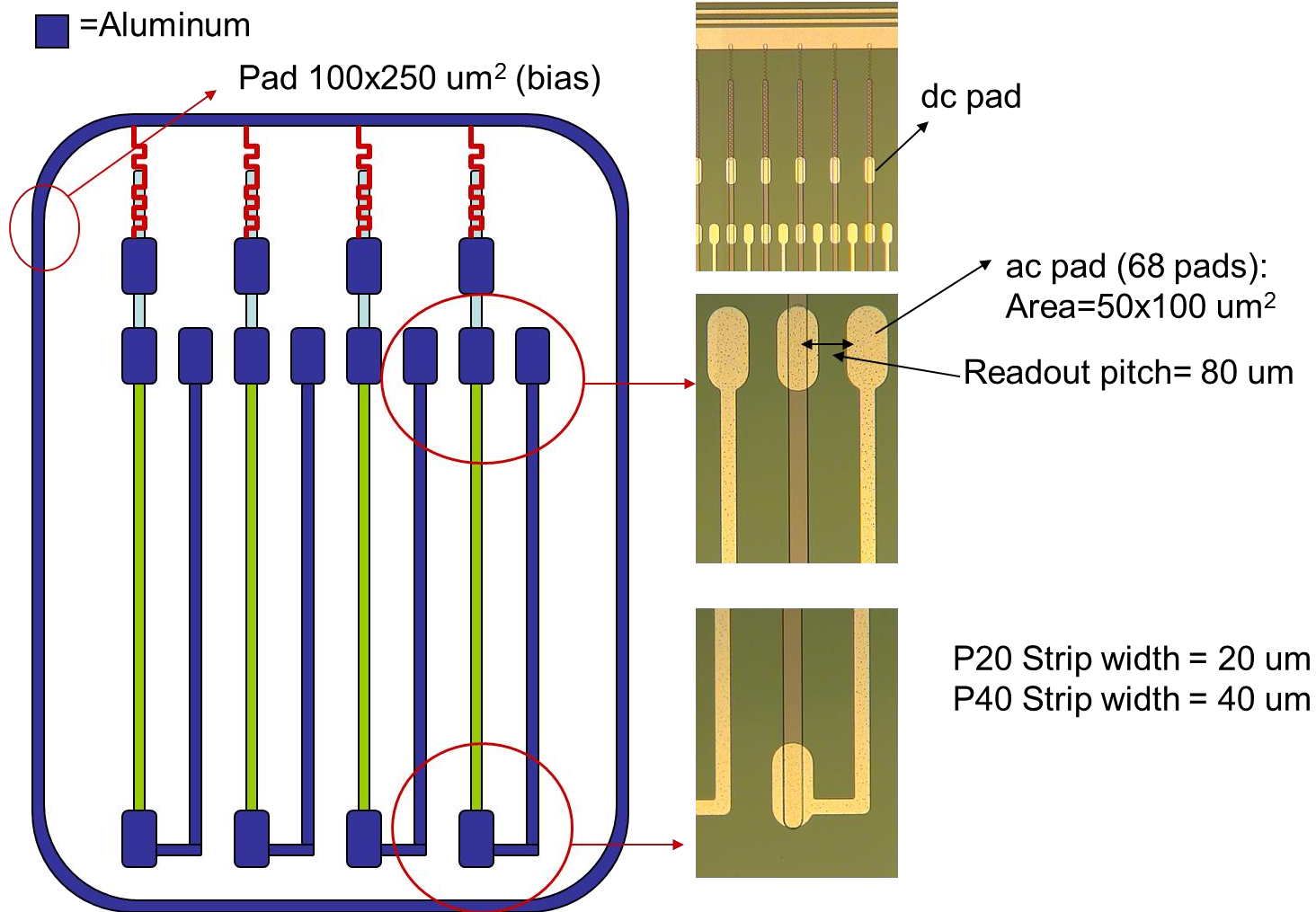


- Test beam at CERN SPS Pion Beam, Nov 2012
- First successful integration and synchronization with AIDA MIMOSA pixel telescope

Defined as $SNR \equiv (S1 + S2) / \sqrt{\sigma1 + \sigma2}$ (drives the spatial resolution)

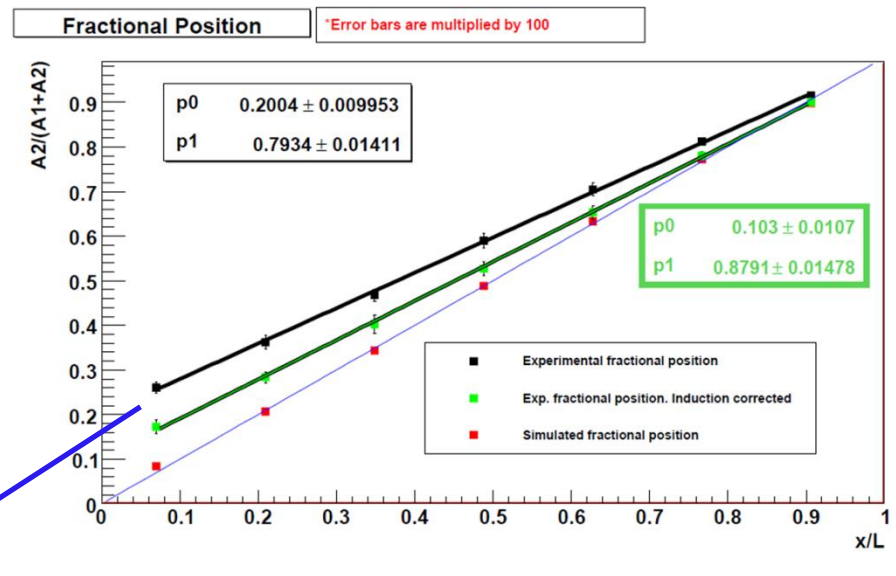
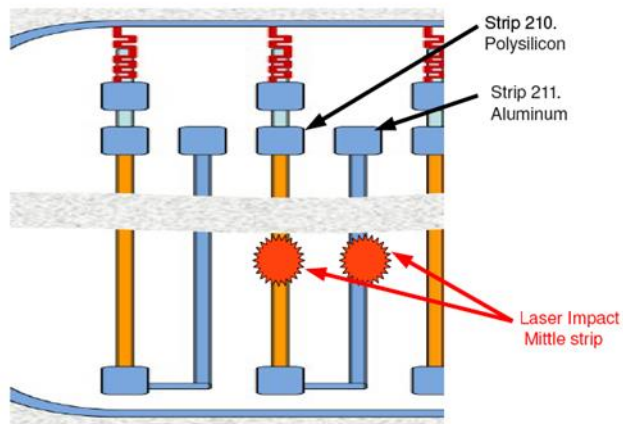


- The charge-division concept on microstrips has been confirmed experimentally, two limitations:
 - Both ends readout difficult to integrate in long ladder (need to combine the information from both ends)
 - Signal attenuation due to the strip resistance (current prototypes 20% signal loss for 2cm length sensor).
- Proposed solutions:
 - **Integrated signal lines** in the sensor to route the signals to the same end.
 - **Reduce the strip resistivity** (limited by the amp. charge resolution) and/or **integrate charge amplification mechanism** in the sensor.

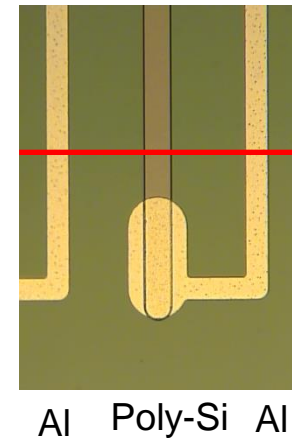
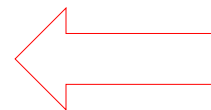
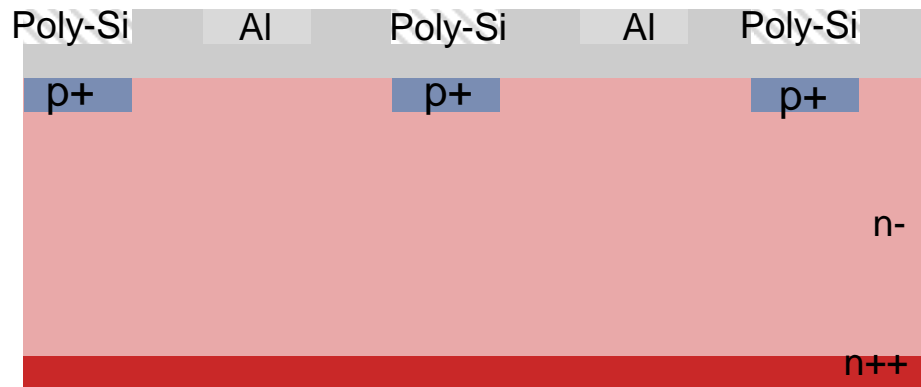


- Induced signal on metallic vias superposed to “direct signal” propagated through polysilicon electrode.

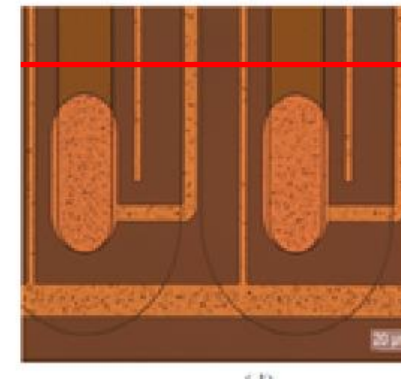
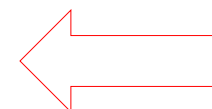
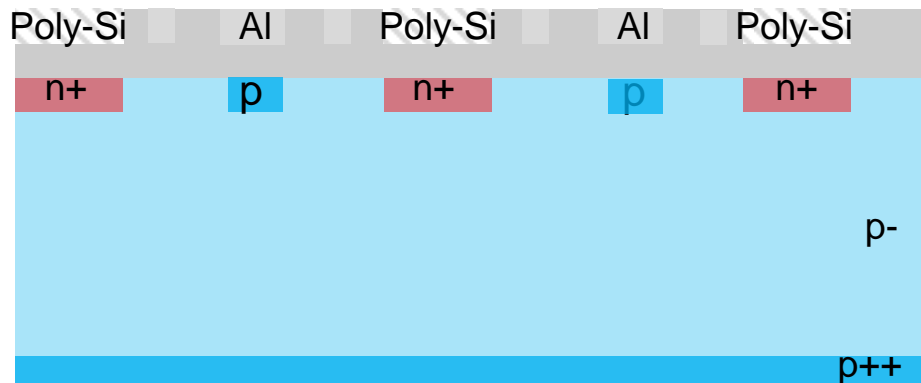
Impact points. Strip Center



Measured Fractional position shows a clear bias



OLD DESIGN

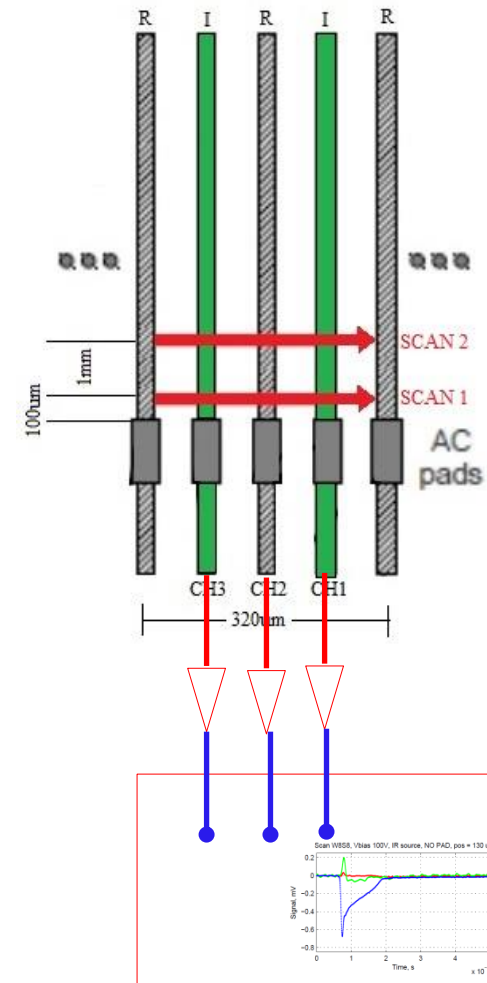
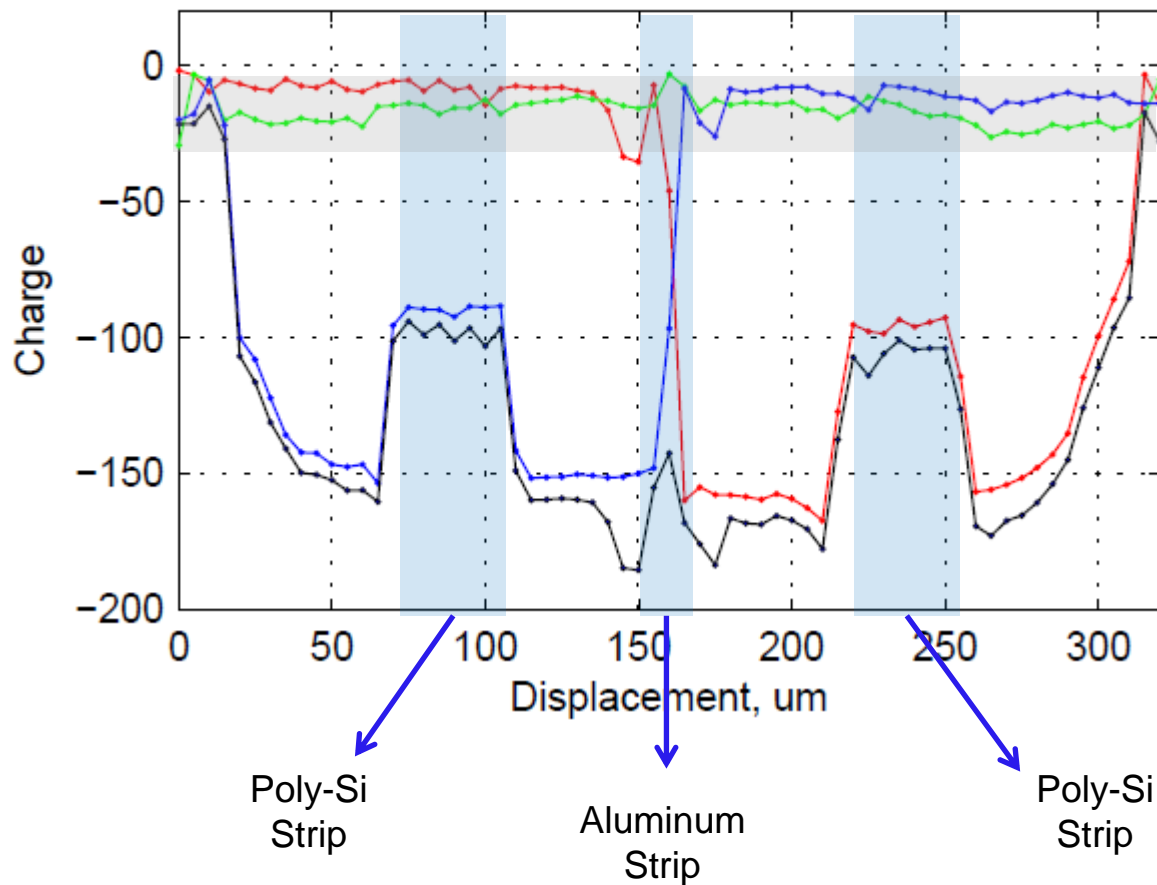


NEW DESIGN
Common P-stop and field plates

Spin-off of FOSTER sensors proposed by KIT at CMS

Flat charge pedestal for Al routing track, suppressed by calibration

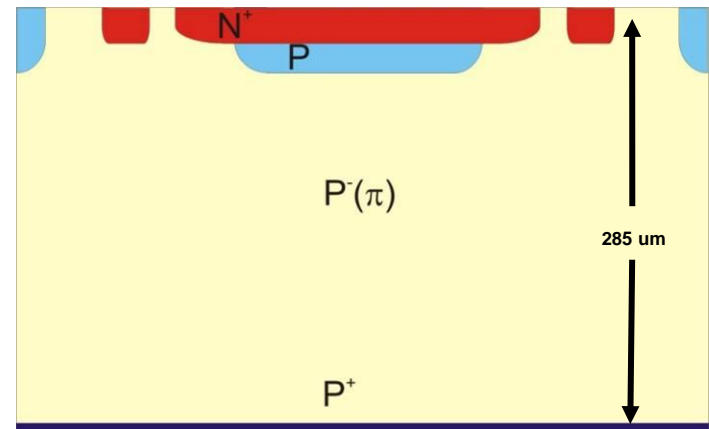
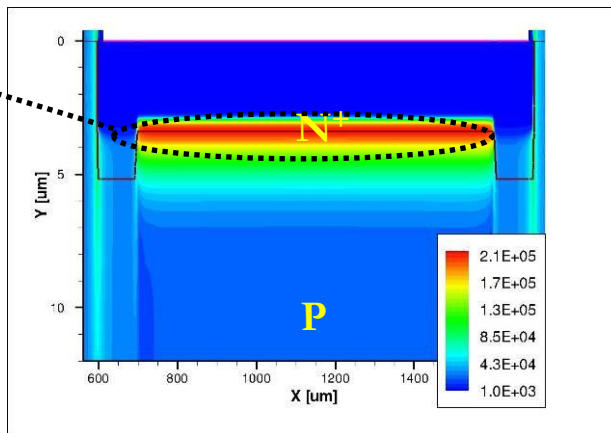
Scan W8S8, Vbias 100V, IR source, NO PAD



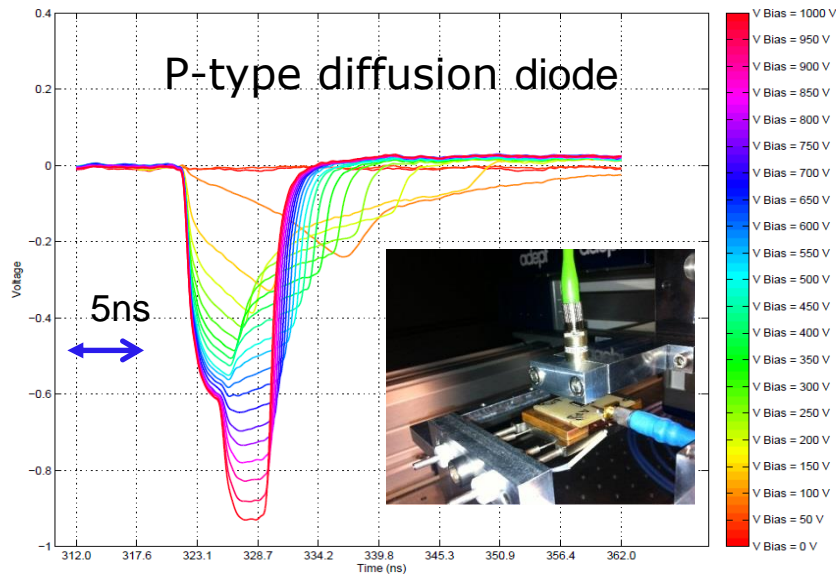
Implanting an n⁺⁺/p⁺/p⁻ junction along the centre of the electrodes. Under reverse bias conditions, a high electric field region is created at this localised region, which can lead to a multiplication mechanism (impact ionization).

Advantages = Thinning while keeping same S/N as standard detectors.

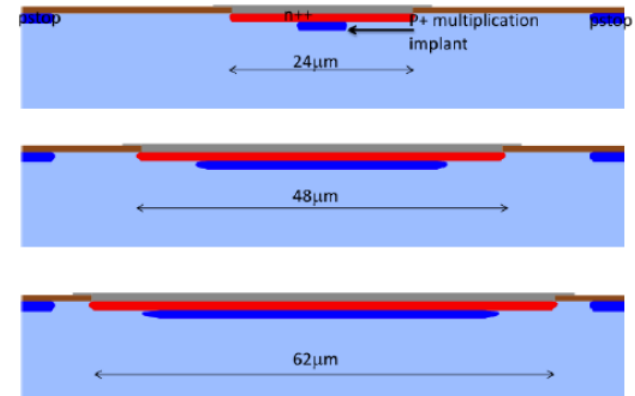
High Electric Field region leading to multiplication



P. Fernandez et al, "Simulation of new p-type strip detectors with trench to enhance the charge multiplication effect in the n-type electrodes", Nuclear Instruments and Methods in Physics Research A 658(2011) 98–102.

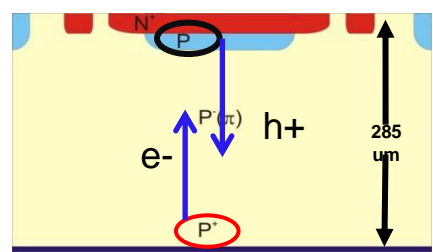


Different strips layout w/ 80 μm pitch:



Marta Baselga 23rd RD50 workshop

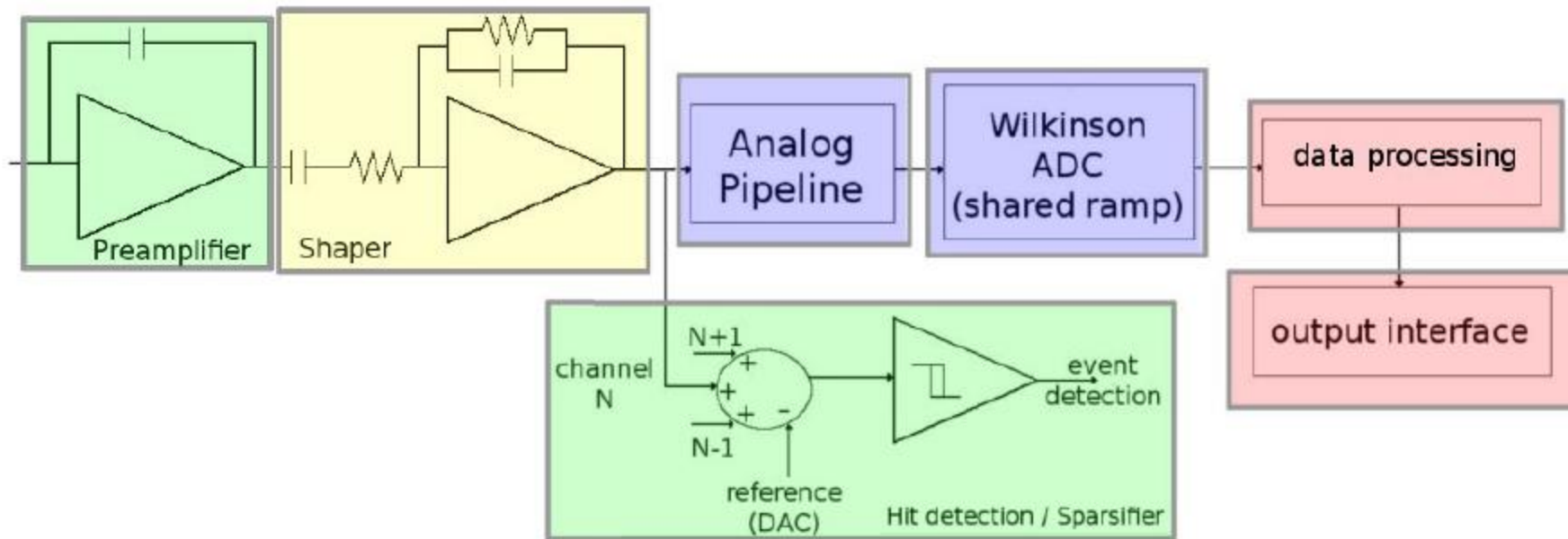
- Excellent results for LGAD diodes
- First strip LGAD prototypes do not show signal amplification.
- New run in progress and new concept to implement: p-on-p sensor (holes readout with electron amplification in a non-structured anode (pad-like) to ensure uniform amplification



TCT Back-side injection (1060 nm)



- Aiming to the design of a long shaping time FE electronics for microstrips (low power consumption)



Designed at schematic level
 Layout of some individual modules

Noise comparison of different frontends

Frontend	A (e-)	B(e-/pF)	Shaping time
This design (*)	377	5,2	2 μ s
APV25	246	36	50 ns
MX6	340	20	
VA1	200	8	1 μ s
Beetle	303	33,6	25 ns
KPix	300	35	

Consumption, area estimation

Block / Part	Power consumption	Area estimation (*) 20 μ m x 2.5mm
Preamplifier	370 μ W	20 μ m x 400 μ m (16%)
Shaper Amp.	120 μ W	20 μ m x 200 μ m (8%)
Sparsifier	70 μ W	20 μ m x 125 μ m (5%)
Comparator	30 μ W	
ADC	100 μ W (estimated)	N/A

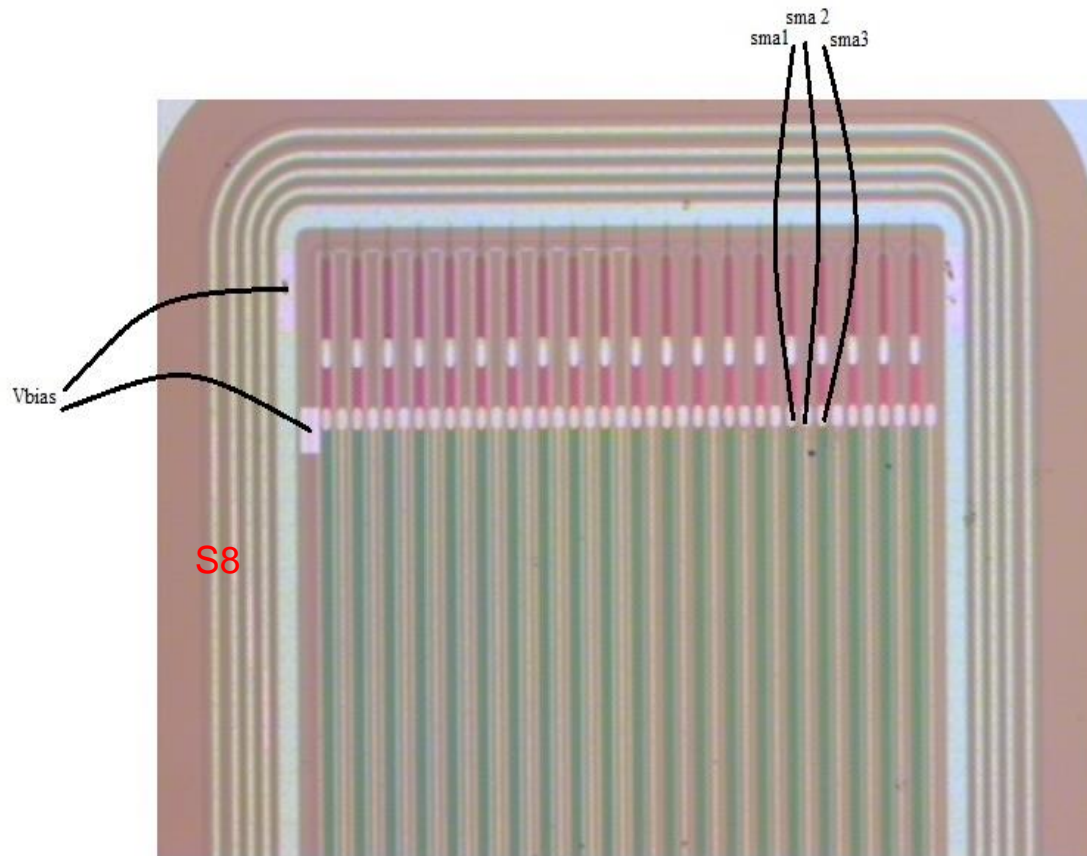
(*): Resistors not included.

(**): Power switching not considered

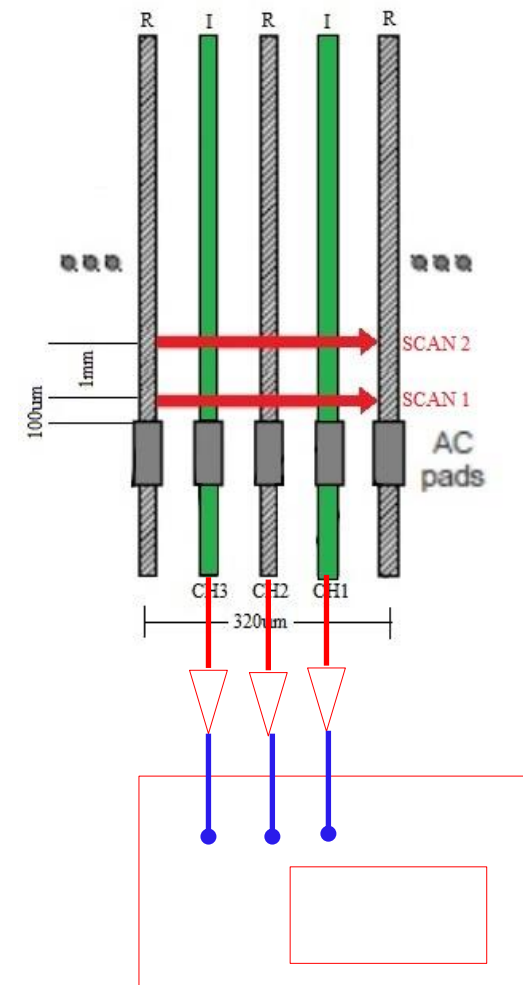
- In parallel with the baseline deliverable additional RTD and networking activity on advanced topics.
- Highlights: New detector concepts, self-monitoring and R/O ASIC.
- Future: AIDA was instrumental in achieving important development milestones but still a few years of work ahead (looking for AIDA-2020)

- **THANK YOU FOR YOUR ATTENTION**

- Time Resolved Readout IR-laser induced (e-TCT like measurement)



No grid Al. Implant – Al routing – Implant



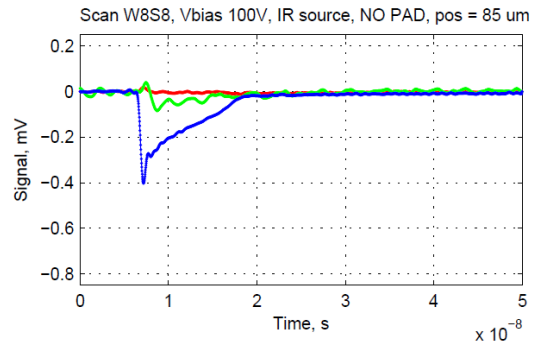


Crosstalk Suppression: Current pulses

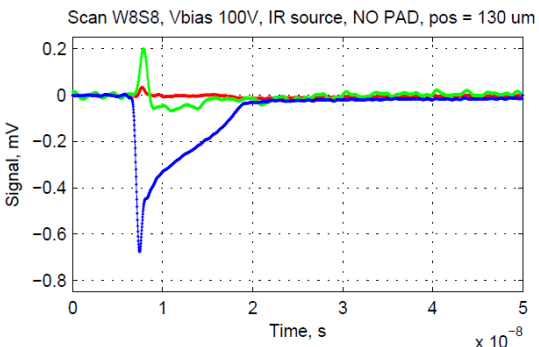
Infrared pico second laser

(fast, 1GHz readout channel)

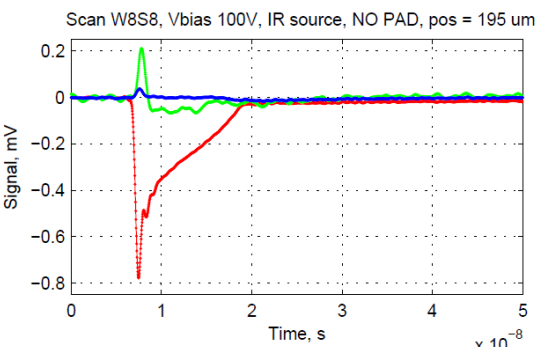
A



B



C



D

